



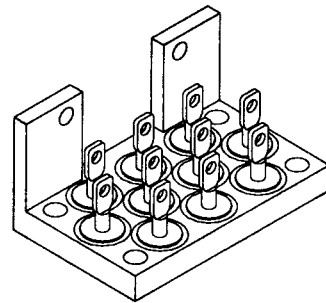
PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

SDA47

**600 AMPS
35 VOLTS
MATCHED POWER
SCHOTTKY
DIODE ARRAY**



Designer's Data Sheet

- FEATURES:**
- Each diode is VF matched to within 20mV of other diodes in array
 - Hermetically sealed Schottky diode cells
 - Hot carrier copper heat sinking mounting bracket
 - Number and configuration of diodes can be customized
 - TX, TXV and Space Level screening

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage	VRRM	35	Volts
	VRWM		
	VR		
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C) note 1	IO	600	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on IO, allow junction to reach equilibrium between pulses, TA=25°C)note 1	IFSM	800	Amps
Operating and storage temperature	Top & Tstg	-65 to +150	°C
Maximum Thermal Resistance Junction to Case	RθJC	1.0	°C/W

Note 1: Per diode

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ELECTRICAL CHARACTERISTICS (per diode)

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop (IF = 50 Adc, TA=25°C, 300µs Pulse)	VF	0.6	Vdc
Instantaneous Forward Voltage Drop (IF = 50 Adc, TA= - 55°C, 300µs Pulse)	VF	0.7	Vdc
Reverse Leakage Current (Rated VR, TA=25°C, 300µs pulse minimum)	IR	50	mA
Reverse Leakage Current (Rated VR, TA=100°C, 300µs pulse minimum)	IR	250	mA
Junction Capacitance (VR = 10 Vdc, TA=25°C, f= 1 MHz)	CJ	3000	pf

CASE OUTLINE:

